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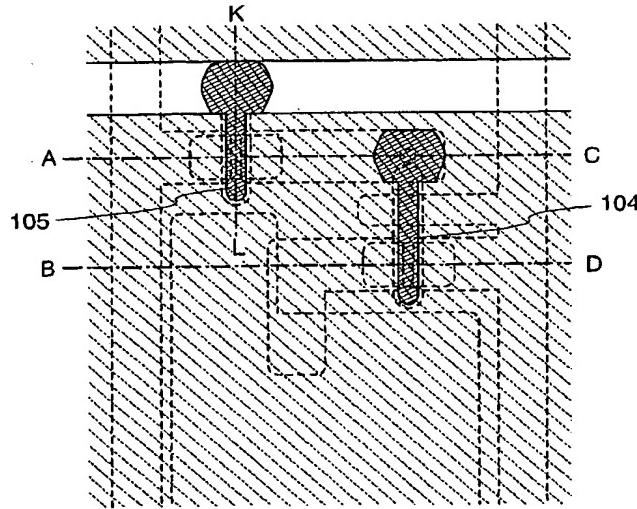
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(54) Title: THIN FILM TRANSISTOR AND DISPLAY DEVICE, AND METHOD FOR MANUFACTURING THEREOF



WO 2005/077549 A1

(57) Abstract: The present invention discloses a display device and a manufacturing method thereof by which a manufacturing process can be simplified. Further, the present invention discloses technique for manufacturing a pattern such as a wiring into a desired shape with good controllability. A method for forming a pattern for constituting the display device according to the present invention comprises the steps of forming a first region and a second region; discharging a composition containing a pattern formation material to a region across the second region and the first region; and flowing a part of the composition discharged to the first region into th